

# DRA4143X (Tentative)

## Silicon PNP epitaxial planar type

For digital circuits

### ■ Packaging

Radial type: 5000 pcs / carton

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	-50	V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	-50	V
Collector current	$I_{\text{C}}$	-100	mA
Total power dissipation	$P_{\text{T}}$	300	mW
Junction temperature	$T_{\text{j}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

### ■ Package

#### • Code

NS-B1-B

#### • Pin Name

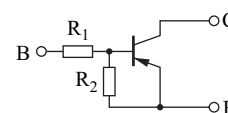
1: Emitter

2: Collector

3: Base

### ■ Marking Symbol: L6

### ■ Internal Connection



Resistance value	$R_1$	4.7	$\text{k}\Omega$
	$R_2$	10	$\text{k}\Omega$

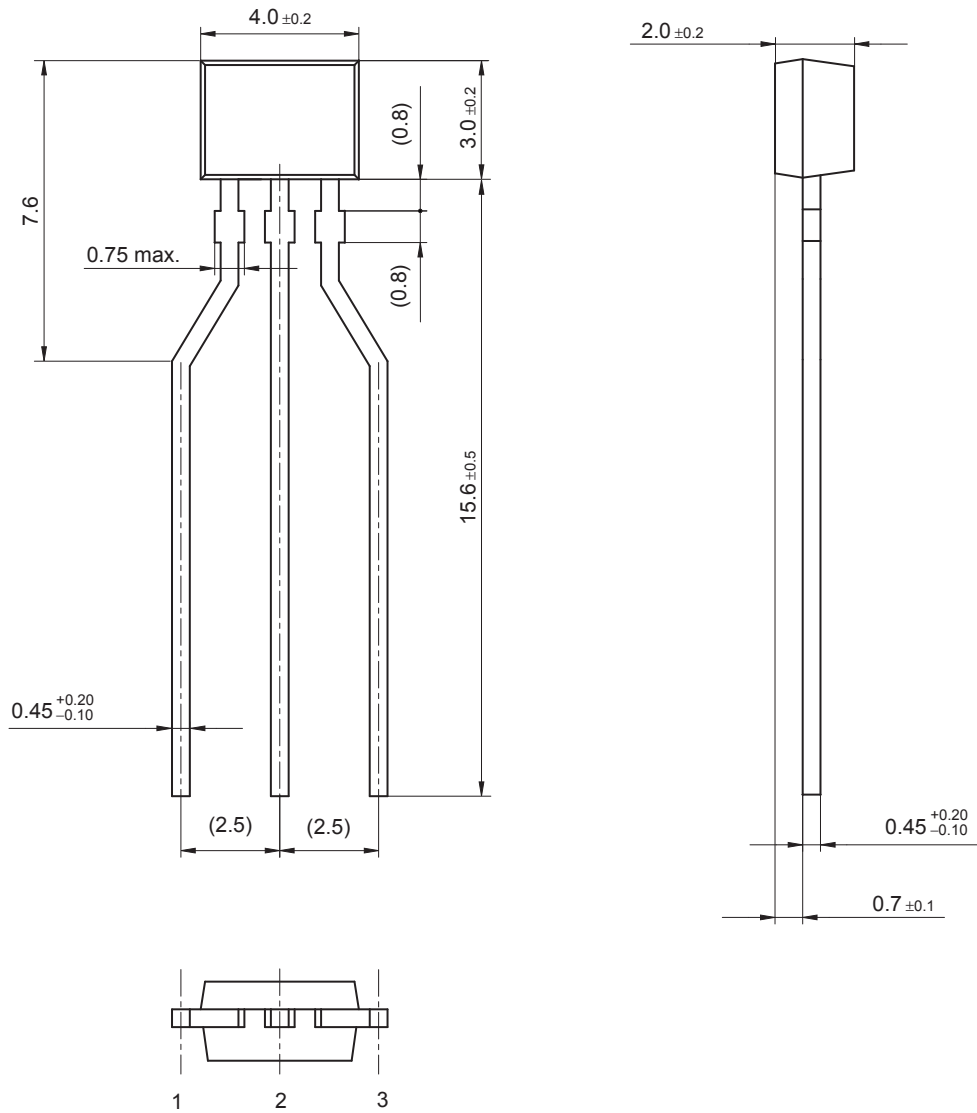
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = -2 \text{mA}, I_{\text{B}} = 0$	-50			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = -50 \text{V}, I_{\text{E}} = 0$			-0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{\text{CEO}}$	$V_{\text{CE}} = -50 \text{V}, I_{\text{B}} = 0$			-0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{\text{EBO}}$	$V_{\text{EB}} = -6 \text{V}, I_{\text{C}} = 0$			-1.0	mA
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = -10 \text{V}, I_{\text{C}} = -5 \text{mA}$	30			—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -10 \text{mA}, I_{\text{B}} = -0.5 \text{mA}$			-0.25	V
Input voltage (ON)	$V_{\text{I(on)}}$	$V_{\text{CE}} = -0.2 \text{V}, I_{\text{C}} = -5 \text{mA}$	-1.7			V
Input voltage (OFF)	$V_{\text{I(off)}}$	$V_{\text{CE}} = -5 \text{V}, I_{\text{C}} = -100 \mu\text{A}$			-0.6	V
Input resistance	$R_1$		-30%	4.7	+30%	$\text{k}\Omega$
Resistance ratio	$R_1 / R_2$		0.37	0.47	0.57	—

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

NS-B1-B

Unit: mm



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